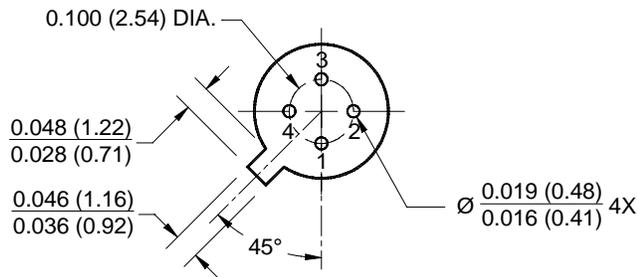
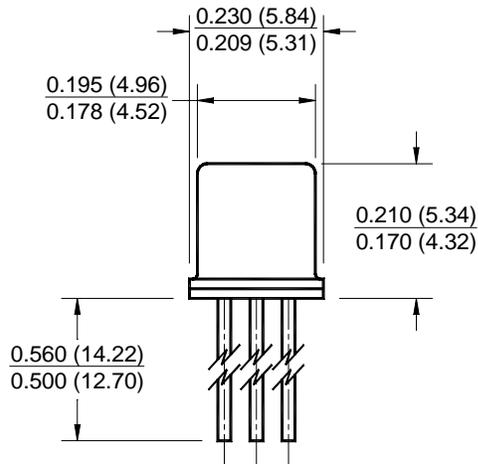
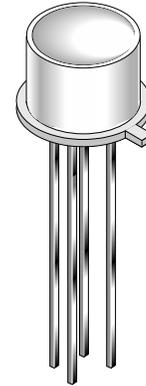


**PACKAGE DIMENSIONS**

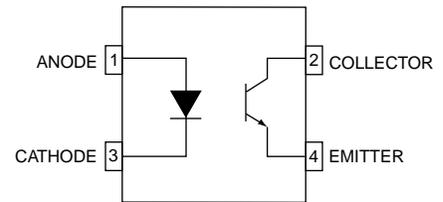


**NOTES:**

1. Dimensions for all drawings are in inches (mm).
2. Tolerance of  $\pm .010$  (.25) on all non-nominal dimensions unless otherwise specified.



**SCHEMATIC**



**DESCRIPTION**

The MCT4 is a standard four-lead, TO-18 package containing a GaAs infrared emitting diode optically coupled to an NPN silicon planar phototransistor.

**FEATURES**

- Hermetically package
- High current transfer ratio; typically 35%
- High isolation resistance;  $10^{11}$  ohms at 500 volts
- High voltage isolation emitter to detector

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_A = 25^\circ\text{C}$ unless otherwise specified)			
Parameter	Symbol	Rating	Unit
Operating Temperature	$T_{OPR}$	-55 to +125	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-65 to +150	$^\circ\text{C}$
Soldering Temperature (Flow)	$T_{SOL-F}$	260 for 10 sec	$^\circ\text{C}$
<b>EMITTER</b>			
Power Dissipation at 25 $^\circ\text{C}$ Ambient (1)	$P_D$	90	mW
Continuous Forward Current	$I_F$	40	mA
Reverse Voltage	$V_R$	3	V
Forward Current - Peak (1 $\mu\text{s}$ pulse, 300 pps)	$I_F(pk)$	3.0	A
<b>DETECTOR</b>			
Power Dissipation 25 $^\circ\text{C}$ Ambient (2)	$P_D$	200	mW
Collector to Emitter Voltage	$V_{CEO}$	30	V
Emitter to Collector Voltage	$V_{ECO}$	7	V
<b>COUPLER</b>			
Total Power Dissipation (3)	$P_D$	250	mW
Isolation Voltage		1000	VDC

<b>ELECTRICAL / OPTICAL CHARACTERISTICS</b> ( $T_A = 25^\circ\text{C}$ )						
<b>INDIVIDUAL COMPONENT CHARACTERISTICS</b>						
Parameters	Test Conditions	Symbol	Min	Typ	Max	Units
<b>EMITTER</b>						
Forward Voltage	$I_F = 40\text{ mA}$	$V_F$		1.30	1.50	V
Reverse Current	$V_R = 3.0\text{ V}$	$I_R$		0.15	10	$\mu\text{A}$
Capacitance	$V = 0\text{ V}$	C		150		pF
<b>DETECTOR</b>						
Breakdown Voltage Collector to Emitter	$I_C = 1.0\text{ mA}, I_F = 0$	$BV_{CEO}$	30			V
Emitter to Collector	$I_E = 100\ \mu\text{A}, I_F = 0$	$BV_{ECO}$	7	12		V
Leakage Current Collector to Emitter	$V_{CE} = 10\text{ V}, I_F = 0$	$I_{CEO}$		5	50	nA
Capacitance Collector to Emitter	$V_{CE} = 0$	$C_{CE}$		2		pF

**NOTE:**

1. Derate power linearly 1.2 mW/ $^\circ\text{C}$  above 25 $^\circ\text{C}$
2. Derate power linearly 2.67 mW/ $^\circ\text{C}$  above 25 $^\circ\text{C}$
3. Derate power linearly 3.3 mW/ $^\circ\text{C}$  above 25 $^\circ\text{C}$

## MCT4

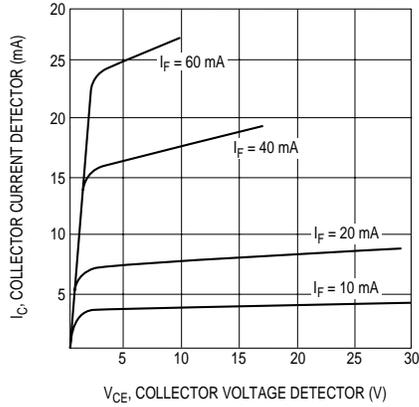
<b>TRANSFER CHARACTERISTICS</b> ( $T_A = 25^\circ\text{C}$ Unless otherwise specified.)						
DC Characteristics	Test Conditions	Symbol	Min	Typ	Max	Units
<b>COUPLED</b>						
DC current Transfer Ratio (note 1)	$V_{CE} = 10\text{ V}, I_F = 10\text{ mA}$	CTR	15	35		%
Saturation Voltage	$I_C = 500\ \mu\text{A}, I_F = 10\text{ mA}$	$V_{CE(SAT)}$		0.1		V
	$I_C = 2\text{ mA}, I_F = 50\text{ mA}$			0.2	0.5	
AC Characteristics	Test Conditions	Symbol	Min	Typ	Max	Units
Capacitance LED to Detector				1.8		pF
Bandwidth (Fig. 5)	Note 2			300		kHz
Rise Time and Fall Time (see operating schematic)	$I_C = 2\text{ mA}, V_{CE} = 10\text{ V}, \text{Note 3}$			2		$\mu\text{s}$

<b>ISOLATION CHARACTERISTICS</b>						
Characteristic	Test Conditions	Symbol	Min	Typ	Max	Units
Isolation Resistance	$V = 500\text{ VDC}$	$R_{ISO}$	$10^{11}$	$10^{12}$		$\Omega$
Breakdown Voltage	Time = 1 sec		1000	1500		VDC

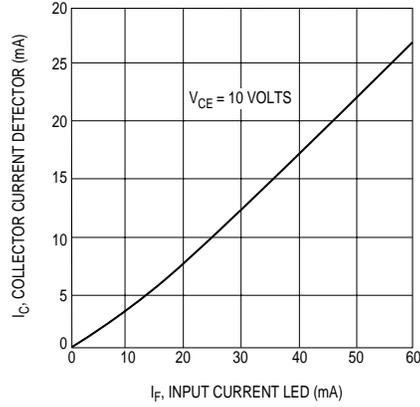
**NOTE:**

1. The current transfer ratio ( $I_C/I_F$ ) is the ratio of the detector collector current to the LED input current with  $V_{CE}$  at 10 volts.
2. The frequency at which  $i_c$  is 3 dB down from the 1 kHz value.
3. Rise time ( $t_r$ ) is the time required for the collector current to increase from 10% of its final value, to 90%. Fall time ( $t_f$ ) is the time required for the collector current to decrease from 90% of its initial value to 10%.

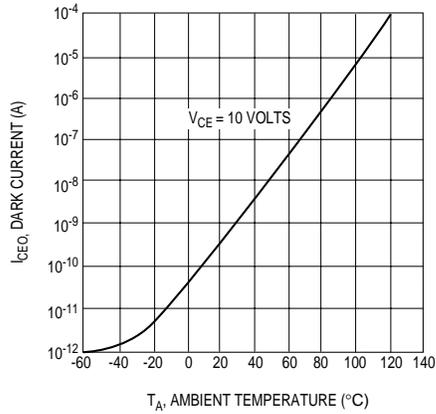
**Figure 1. Detector Output Characteristics**



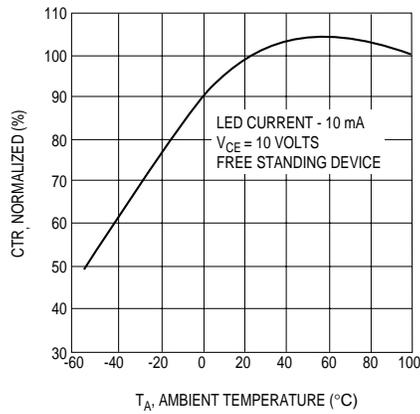
**Figure 2. Input Current vs. Output Current**



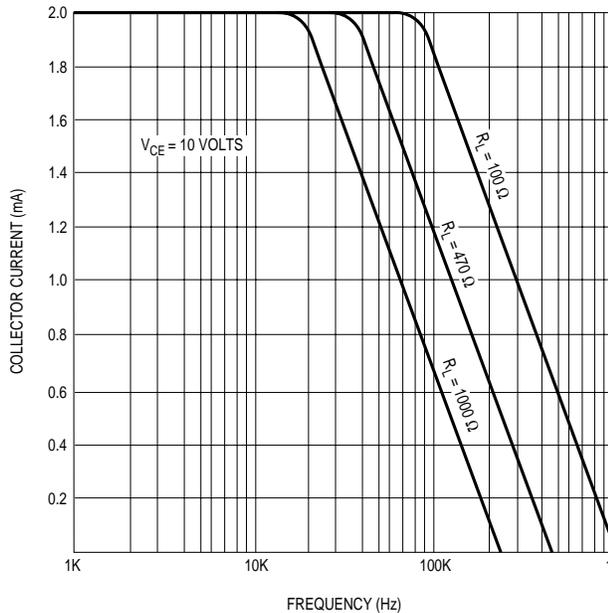
**Figure 3. Dark Current vs. Temperature**



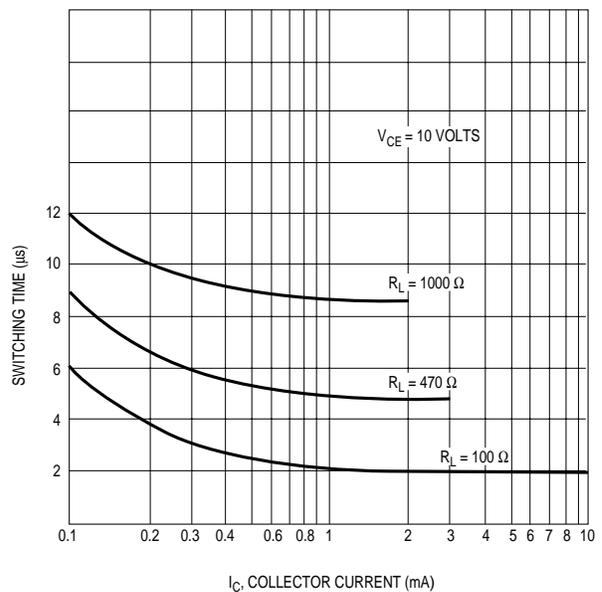
**Figure 4. Current Output vs. Temperature**

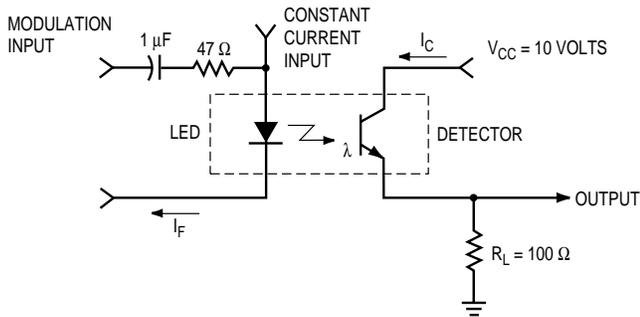


**Figure 5. Output vs. Frequency**

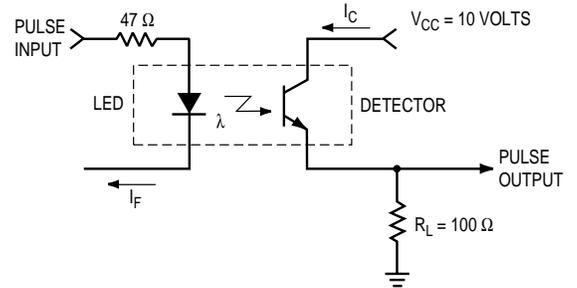


**Figure 6. Switching Time vs. Collector Current**





**Figure 7. Modulation Circuit Used to Obtain Output vs. Frequency Plot**



**Figure 8. Circuit Used to Obtain Switching Time vs. Collector Current Plot**

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